

Claims

- [c1] What is claimed is:
1. A solder bump structure and laser repair process for memory device, comprising:
 - providing a semiconductor wafer, which comprises a substrate, an integrated circuit, and at least one bump pad formed on the substrate and electrically connected with the integrated circuit;
 - forming a first dielectric layer on a surface of the bump pad;
 - performing an etching process to form a contact hole in the first dielectric layer and to expose a portion of the bump pad;
 - forming a second dielectric layer on a surface of the semiconductor wafer outside of the contact hole;
 - performing an under bump metallurgy (UBM) process so as to form a metal layer on a surface of the contact hole;
 - forming a solder bump on the metal layer corresponding to the contact hole;
 - and
 - performing a connection process to complete connection of the semiconductor wafer and a packaging board.
 - [c2] 2. The solder bump structure and laser repair process for memory device of claim 1 wherein the semiconductor wafer further comprises:
 - a plurality of fuses electrically connected with the integrated circuit;
 - at least one alignment key; and
 - a silicon oxide layer formed on a surface of the fuses and the alignment key.
 - [c3] 3. The solder bump structure and laser repair process for memory device of claim 2 wherein the method of forming the second dielectric layer on the surface of the semiconductor wafer outside of the contact hole comprises:
 - forming the second dielectric layer on the surface of the semiconductor wafer;
 - and
 - performing a photo-etching-process (PEP) to remove portions of the second dielectric layer formed on the surface of the contact hole, the fuses, and the alignment key.

- [c4] 4.The solder bump structure and laser repair process for memory device of claim 2 wherein the integrated circuit further comprises an embedded memory array.
- [c5] 5.The solder bump structure and laser repair process for memory device of claim 1 wherein a circuit probing and a laser repair process are performed after the formation of the solder bump, and a probing tip is used to perform the circuit probing process by electrically connecting with the solder bump.
- [c6] 6.The solder bump structure and laser repair process for memory device of claim 1 wherein the second dielectric layer is composed of insulating materials such as benzocyclobutene (BCB), polyimide (PI), and BCB+PI.
- [c7] 7.A solder bump structure and laser repair process for memory device, comprising:
providing a semiconductor wafer, which comprises a substrate, an integrated circuit, and at least one bump pad formed on the substrate and electrically connected with the integrated circuit;
forming a dielectric layer on a surface of the bump pad;
performing an etching process to form a contact hole in the dielectric layer and to expose a portion of the bump pad;
performing an under bump metallurgy (UBM) process so as to form a metal layer on a surface of the contact hole;
forming a solder bump on the metal layer corresponding to the contact hole;
and
performing a connection process to complete connection of the semiconductor wafer and a packaging board.
- [c8] 8.The solder bump structure and laser repair process for memory device of claim 7 wherein the semiconductor wafer further comprises:
a plurality of fuses electrically connected with the integrated circuit;
at least one alignment key; and
a silicon oxide layer formed on a surface of the fuses and the alignment key.
- [c9] 9.The solder bump structure and laser repair process for memory device of

claim 8 wherein the integrated circuit further comprises an embedded memory array.

[c10] 10.The solder bump structure and laser repair process for memory device of claim 7 wherein a circuit probing and a laser repair process are performed after the formation of the solder bump, and a probing tip is used to perform the circuit probing process by electrically connecting with the solder bump.